## NSN 5962-01-311-2908

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-311-2908 **Body Length:** 0.840 inches **Body Width:** 0.310 inches **Body Height:** 0.185 inches **Maximum Power Dissipation Rating:** 739.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **End Application:** Forward card box assembly **Features Provided:** Monolithic and schottky and programmable and bipolar **Inclosure Material:** Ceramic **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 6 input **Case Outline Source And Designator:** D-2 mil-m-38510 **Terminal Surface Treatment:** Solder Voltage Rating And Type Per Characteristic: 7.0 volts total supply **Time Rating Per Chacteristic:** 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, low to high level output **Memory Device Type:** Prom **Terminal Type And Quantity:** 16 printed circuit Shelf Life: N/a

Demilitarization:

**Unit Of Measure:** 

Yes - demil/mli

## NSN 5962-01-311-2908

Memory Microcircuit - Page 2 of 2



Fiig:

A458a0